## Defects Activity in Lead Halide Perovskites: a Computational Perspective



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**CNR-ISTM** 



• **Defects modelling** in Lead-Halide Perovskites (ACS Energy Lett. 2018, 3, 2206-2222)

• Defects chemistry and Defects Tolerance of Lead-Halide Perovskites (Energy Environ. Sci. 2018, 11, 702-713)

• Role of surfaces and defects reactivity (ACS Energy Lett. 2019, 4, 779-785)

## **Introduction – Perovskites Solar Cells**

- Structure ABX<sub>3</sub>
  - A = organic/inorganic cation
  - B = metal (Pb)
  - X = halide (I, Br, Cl)
- Direct band-gap semiconductor (1.2 to 1.6 eV)
- Low cost manufacturing (solution chemistry)
- Thin films technology (high defects densities)





#### High efficiencies (24%)

- Long-lived carriers
- High defects tolerance

substitutional impurity

vacancy interstitial impurity

## **Defects and Charge Traps in Perovskites**



- Native defects play a prominent role in PL properties of HOIP (*Shockley et al. Phys. Rev.* **1952**, *87*, *835-842*)
- Defects tolerance: PL properties not strongly affected even in polycrystalline HOIP (~ 10<sup>16</sup> cm<sup>-3</sup>) (*Leijtens et al. Energy Environ. Sci.* 2016, 9, 3472-3481)

#### Defects activity both in the bulk and on the surface of LHP

Charge Traps: loss of efficiency

#### **First-principles DFT modelling**

### **Defects - Essentials**

**Native defects:** natural products of crystal growth (entropy gain) **Different states of charge**  $\Delta G_{def} = \Delta H_{def} - T\Delta S_{def} \qquad \Delta H_{def} > 0$  $\Delta S_{def} > 0$ 2.0I<sub>i</sub> in MAPbI<sub>3</sub> 1.5 **Defects stability: Defects formation energies (DFE)** (0/-) (+/0)DFE (eV)  $DFE(X^{q}) = E(X^{q}) - E(bulk) - \sum_{i} n_{i}\mu_{i} + q(E_{F} + VBM + \Delta V) + E^{q}$  $I_i^0$ 0.5 (+/-) 0.0Thermodynamics ionization levels (TIL) **I**;-٠ -0.5 I-rich 0.5 1.5  $\varepsilon(q/q') = \frac{DFE(D^{q}, E_{F}=0) - DFE(D^{q'}, E_{F}=0)}{\alpha' - \alpha}$  $E_{F}(eV)$ **Deep ionization levels: charge trapping Different conditions of growth** ۲

### **Defects – Band gap problem**

$$DFE(X_q) = E^{def}(X_q) - E^{prist} + \sum_i n_i \mu_i + q(E_F + E_{VB} + \Delta V) + E^q$$

#### **MAPbl**<sub>3</sub> - Thermodynamic ionization levels



Meggiolaro et al. ACS Energy Lett. 2018, 3, 2206



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## **Trapping properties - Thermodynamic ionization levels**

- I<sub>i</sub> and V<sub>Pb</sub> are deep traps. They can trap both electrons or holes depending on their oxidation states
- I<sub>i</sub> and V<sub>Pb</sub> are associated to undercoordinated iodines (I-rich environment)
- Iodine chemistry dominates the charge trapping activity in MAPbl<sub>3</sub>
  - Iodine chemistry Charge Traps -0.5



#### Lead chemistry Shallow levels

- **V**<sub>I</sub> and Pb<sub>i</sub> show shallow levels.
- Inert in charge trapping processes
- V<sub>1</sub> and Pb<sub>i</sub> are associated to undercoordinated Pb (Pb-rich environment)
  - MA defects do not couple with band edges (shallow)

#### **Iodine Chemistry determines the charge traps activity in LHP**

Meggiolaro et al. Energy Environ. Sci. 2018, 11, 702-713

## Metastable and emissive traps in MAPI

#### Theory

- Long-lived electrons traps (μs), non-radiative decay: I<sub>i</sub><sup>+</sup>
  - Short-lived holes traps, radiative decay: I<sub>i</sub><sup>-</sup>





#### MAPbl<sub>3</sub> - Experiments



Meggiolaro et al. Energy Environ. Sci. 2018, 11, 702-713



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## Surface defects activity

- Defects are stabilized at surfaces
- Enhanced migration and trapping activity





## Model: Dimensions of NCs and surface availability strongly affect DFEs and diffusion of defects

 $DFE_{av} = (d_{surf} 6L^2 DFE_{surf} + d_{bulk} L^3 DFE_{bulk}) / (d_{surf} 6L^2 + d_{bulk} L^3)$ 



# Passivation of surface sites limits defects formation and migration

 $\sigma = T^m e^2 D_0 / kT \exp(-\Delta H^{\neq} / kT) \exp(-DFE/kT)$ 

Meggiolaro et al. ACS Energy Lett. 2019, 4, 779-785

## Photostability of LHP

Photostability and PCEs of LHP are influenced by temperature and light exposure

PLE

**PLD** 

Light repetition rate

#### Temperature





## Surface passivation to stabilize PVK thin films

#### Passivation of surfaces with oxygen-containing agents / polymers, such as PEO or TOPO

Theory

#### **Experiments**

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Iodine interstitial DFE increase by 0.1 eV



Motti, S. G.; Meggiolaro, D. et al. *Nat. Photon.* **2019**, 13, 532-539

Thank you!